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Kind regards,

Team Nexperia

# PEMB16; PUMB16

## PNP/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = 47 kΩ

Rev. 03 — 31 August 2009 Product data sheet

## 1. Product profile

### 1.1 General description

PNP/PNP resistor-equipped transistors

Table 1. Product overview

| Type number | Package | | NPN/PNP complement | NPN/NPN complement |
|---|---|---|---|---|
| | NXP | JEITA | | |
| PEMB16 | SOT666 | - | PEMD16 | PEMH16 |
| PUMB16 | SOT363 | SC-88 | PUMD16 | PUMH16 |

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

### 1.4 Quick reference data

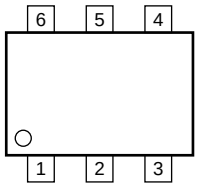
Table 2. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{CEO}$ | collector-emitter voltage | open base | - | - | –50 | V |
| $I_O$ | output current | | - | - | –100 | mA |
| R1 | bias resistor 1 (input) | | 15.4 | 22 | 28.6 | kΩ |
| R2/R1 | bias resistor ratio | | 1.7 | 2.1 | 2.6 | |

## 2. Pinning information

**Table 3. Pinning**

| Pin | Description | Simplified outline | Symbol |
|---|---|---|---|
| 1 | GND (emitter) TR1 | | |
| 2 | input (base) TR1 | | |
| 3 | output (collector) TR2 | | |
| 4 | GND (emitter) TR2 | | |
| 5 | input (base) TR2 | | |
| 6 | output (collector) TR1 | | |

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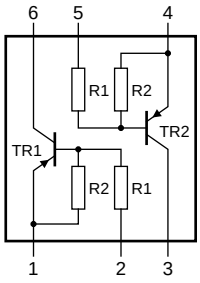


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## 3. Ordering information

**Table 4. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PEMB16 | - | plastic surface mounted package; 6 leads | SOT666 |
| PUMB16 | SC-88 | plastic surface mounted package; 6 leads | SOT363 |

## 4. Marking

**Table 5. Marking codes**

| Type number | Marking code[1] |
|---|---|
| PEMB16 | 5G |
| PUMB16 | B*7 |

[1] * = -: made in Hong Kong
* = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| **Per transistor** | | | | | | |
| $V_{CBO}$ | collector-base voltage | open emitter | | - | –50 | V |
| $V_{CEO}$ | collector-emitter voltage | open base | | - | –50 | V |
| $V_{EBO}$ | emitter-base voltage | open collector | | - | –5 | V |
| $V_I$ | input voltage | | | | | |
| | positive | | | - | +7 | V |
| | negative | | | - | –40 | V |
| $I_O$ | output current | | | - | –100 | mA |
| $I_{CM}$ | peak collector current | | | - | –100 | mA |
| $P_{tot}$ | total power dissipation | $T_{amb} \leq 25$ °C | | | | |
| | SOT363 | | [1] | - | 200 | mW |
| | SOT666 | | [1] [2] | - | 200 | mW |
| $T_{stg}$ | storage temperature | | | –65 | +150 | °C |
| $T_j$ | junction temperature | | | - | 150 | °C |
| $T_{amb}$ | ambient temperature | | | –65 | +150 | °C |
| **Per device** | | | | | | |
| $P_{tot}$ | total power dissipation | $T_{amb} \leq 25$ °C | | | | |
| | SOT363 | | [1] | - | 300 | mW |
| | SOT666 | | [1] [2] | - | 300 | mW |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **Per transistor** | | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | $T_{amb} \leq 25$ °C | | | | | |
| | SOT363 | | [1] | - | - | 625 | K/W |
| | SOT666 | | [1] [2] | - | - | 625 | K/W |
| **Per device** | | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | $T_{amb} \leq 25$ °C | | | | | |
| | SOT363 | | [1] | - | - | 416 | K/W |
| | SOT666 | | [1] [2] | - | - | 416 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

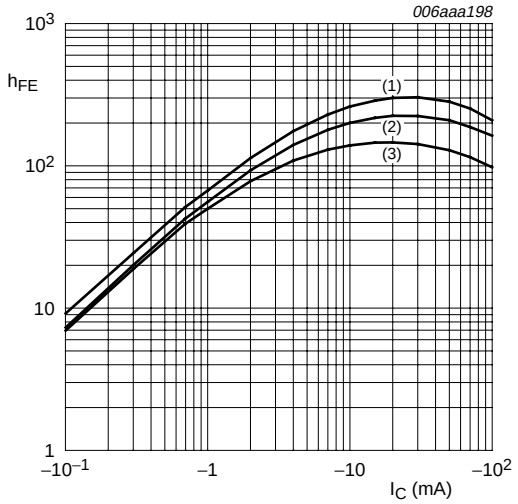
[2] Reflow soldering is the only recommended soldering method.

# 7. Characteristics

**Table 8. Characteristics**

*$T_{amb}$ = 25 °C unless otherwise specified.*

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Per transistor** | | | | | | |
| $I_{CBO}$ | collector-base cut-off current | $V_{CB}$ = –50 V; $I_E$ = 0 A | - | - | –100 | nA |
| $I_{CEO}$ | collector-emitter cut-off current | $V_{CE}$ = –30 V; $I_B$ = 0 A | - | - | –1 | µA |
| | | $V_{CE}$ = –30 V; $I_B$ = 0 A; $T_j$ = 150 °C | - | - | –50 | µA |
| $I_{EBO}$ | emitter-base cut-off current | $V_{EB}$ = –5 V; $I_C$ = 0 A | - | - | –120 | µA |
| $h_{FE}$ | DC current gain | $V_{CE}$ = –5 V; $I_C$ = –5 mA | 80 | - | - | |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C$ = –10 mA; $I_B$ = –0.5 mA | - | - | –150 | mV |
| $V_{I(off)}$ | off-state input voltage | $V_{CE}$ = –5 V; $I_C$ = –100 µA | - | –0.8 | –0.5 | V |
| $V_{I(on)}$ | on-state input voltage | $V_{CE}$ = –0.3 V; $I_C$ = –2 mA | –2 | –1.1 | - | V |
| R1 | bias resistor 1 (input) | | 15.4 | 22 | 28.6 | kΩ |
| R2/R1 | bias resistor ratio | | 1.7 | 2.1 | 2.6 | |
| $C_c$ | collector capacitance | $V_{CB}$ = –10 V; $I_E$ = $i_e$ = 0 A; f = 1 MHz | - | - | 3 | pF |



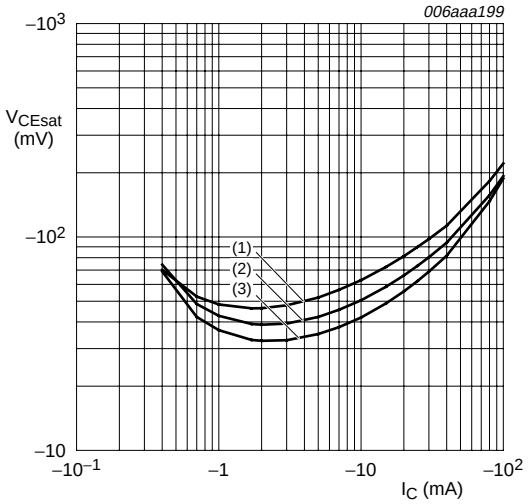

$V_{CE}$ = −5 V

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = −40 °C

**Fig 1. DC current gain as a function of collector current; typical values**



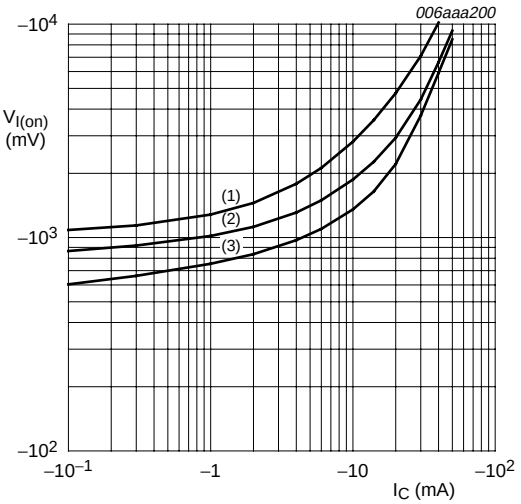

$I_C/I_B$ = 20

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = −40 °C

**Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values**



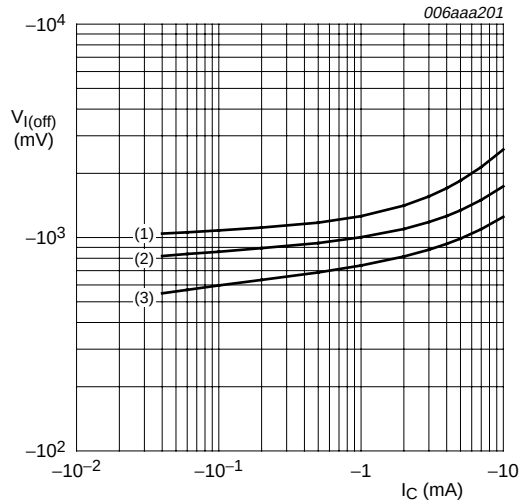

$V_{CE}$ = −0.3 V

(1) $T_{amb}$ = −40 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = 100 °C

**Fig 3. On-state input voltage as a function of collector current; typical values**




$V_{CE}$ = −5 V

(1) $T_{amb}$ = −40 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = 100 °C

**Fig 4. Off-state input voltage as a function of collector current; typical values**

## 8. Package outline

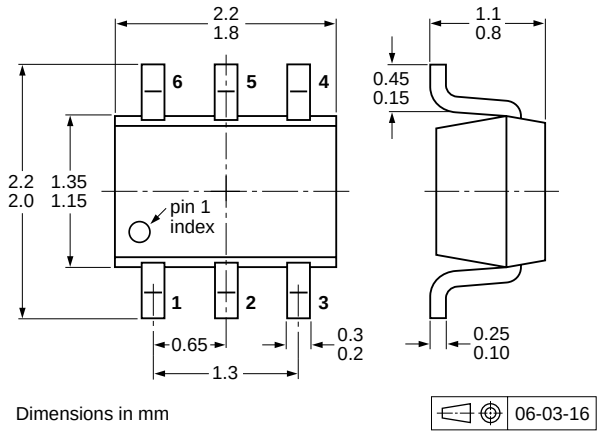



Fig 5. Package outline SOT363 (SC-88)

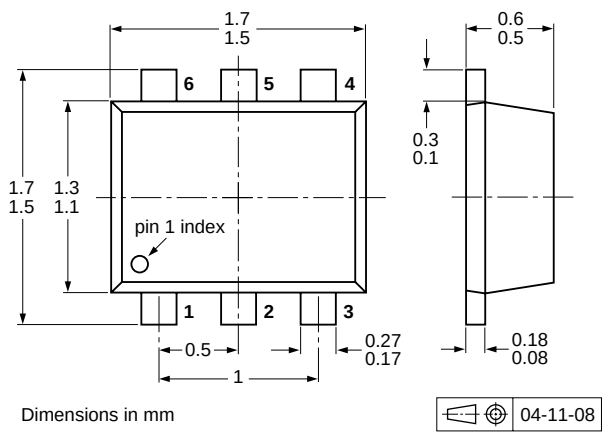



Fig 6. Package outline SOT666

## 9. Packing information

**Table 9. Packing methods**

*The indicated -xxx are the last three digits of the 12NC ordering code.* [1]

| Type number | Package | Description | Packing quantity | | |
|---|---|---|---|---|---|
| | | | 3000 | 4000 | 10000 |
| PEMB16 | SOT666 | 4 mm pitch, 8 mm tape and reel; | - | -115 | - |
| PUMB16 | SOT363 | 4 mm pitch, 8 mm tape and reel; T1 [2] | -115 | - | -135 |
| PUMB16 | SOT363 | 4 mm pitch, 8 mm tape and reel; T2 [3] | -125 | - | -165 |

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

## 10. Revision history

**Table 10. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| PEMB16_PUMB16_3 | 20090831 | Product data sheet | - | PEMB16_PUMB16_2 |
| Modifications: | • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.<br>• Figure 5 “Package outline SOT363 (SC-88)”: updated | | | |
| PEMB16_PUMB16_2 | 20050610 | Product data sheet | - | PUMB16_1 |
| PUMB16_1 | 20031103 | Product specification | - | - |

# 11. Legal information

## 11.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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